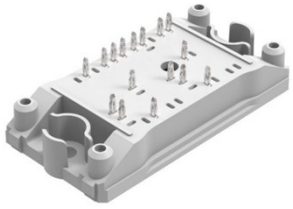
Vincotech

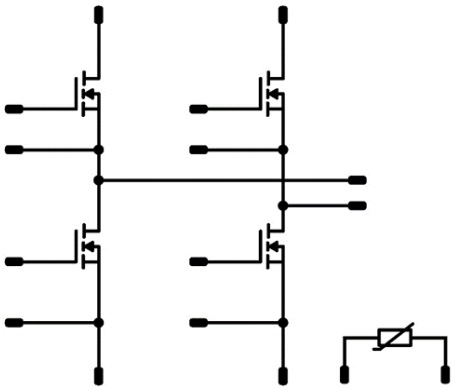
10-PC124PA040MR-L638F18Y
datasheet

fastPACK 0 H **1200 V / 40 mΩ**

Features
- H-bridge or 2x half-bridge
- SiC MOS
- Thermistor

flow 0 12 mm housing


Target applications
- Power Supply

Schematic


Types
- 10-PC124PA040MR-L638F18Y

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
H-Bridge Switch				
Drain-source voltage	V_{DSS}		1200	V
Drain current	I_D	$T_j = T_{jmax}$ T_s = 80 °C	28	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	137	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	68	W
Gate-source voltage	V_{GSS}		-4/22	V
Maximum Junction Temperature	T_{jmax}		175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
		AC Voltage t_p = 1 min	2500	V
Creepage distance			min. 12,7	mm
Clearance			9,57	mm
Comparative Tracking Index	CTI		> 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
H-Bridge Switch										
Static										
Drain-source on-state resistance	$r_{DS(on)}$		18		20	25 125 150		39 52 60	50	mΩ
Gate-source threshold voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$		10	0,01	25	2,7		5,6	V
Gate to Source Leakage Current	I_{GSS}		-4/22	0		25			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25			10	µA
Internal gate resistance	r_g							7		Ω
Gate charge	Q_g		18	600	20	25		107		nC
Gate to source charge	Q_{GS}							22		
Gate to drain charge	Q_{GD}							41		
Short-circuit input capacitance	C_{iss}	f= 1MHz	0	800		25		1337		pF
Short-circuit output capacitance	C_{oss}							76		
Reverse transfer capacitance	C_{rss}							27		
Reverse Diode Static										
Diode forward voltage	VSD		0		20	25		3,2		V
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,41		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	-4 / 16	700	33	25 125 150		16 15 15		ns
Rise time	t_r					25 125 150		7 7 7		
Turn-off delay time	$t_{d(off)}$					25 125 150		46 52 53		
Fall time	t_f					25 125 150		8 10 8		
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 0,5 µC Q_{rFWD} = 0,5 µC Q_{rFWD} = 0,6 µC				25 125 150		0,598 0,582 0,601		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,334 0,352 0,352		

Characteristic Values

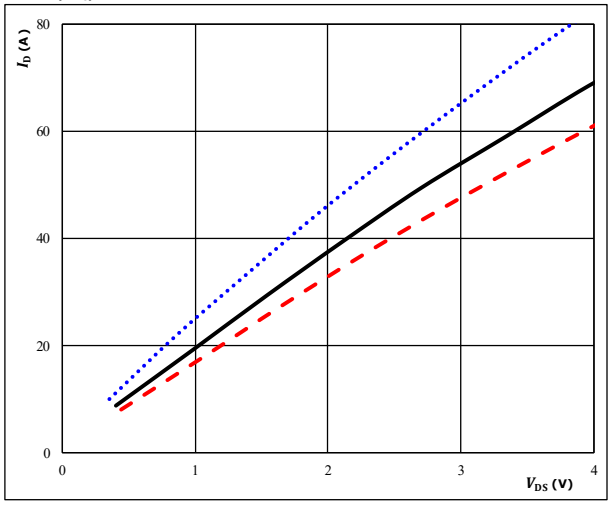
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
H-Bridge Switch										
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 3744 A/µs di/dt = 5388 A/µs di/dt = 3349 A/µs	-4 / 16	700	33	25 125 150		34 33 33		A
Reverse recovery time	t_{rr}					25 125 150		21 23 24		ns
Recovered charge	Q_r					25 125 150		0,474 0,516 0,558		µC
Reverse recovered energy	E_{rec}					25 125 150		0,131 0,157 0,170		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		3782 3764 5296		A/µs
Thermistor										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		5		mW
Power dissipation constant						25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %				25		3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %				25		4000		K
Vincotech NTC Reference									I	

H-Bridge Switch Characteristics

figure 1. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$

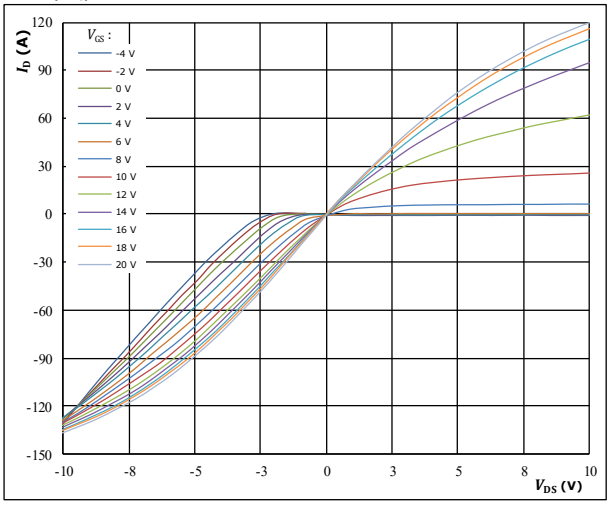


t_p =	250	µs		25 °C	
V_{GS} =	18	V	T_j:	125 °C	
				150 °C	

figure 2. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$

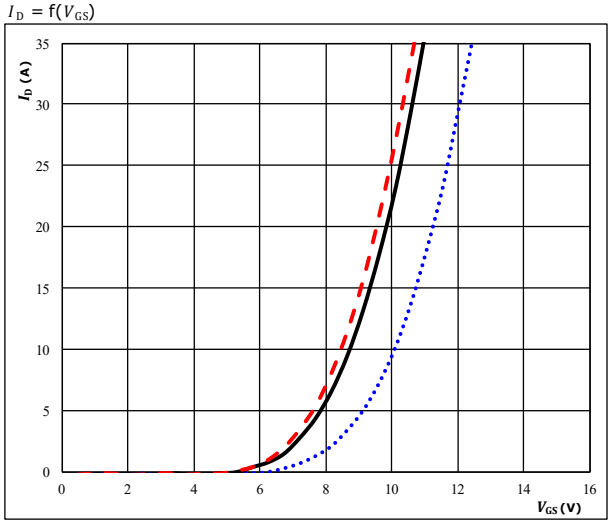


t_p =	250	µs
T_j =	150	°C
V_{GS} from	-4 V to 20 V in steps of 2 V	

figure 3. **MOSFET**

Typical transfer characteristics

$I_D = f(V_{GS})$

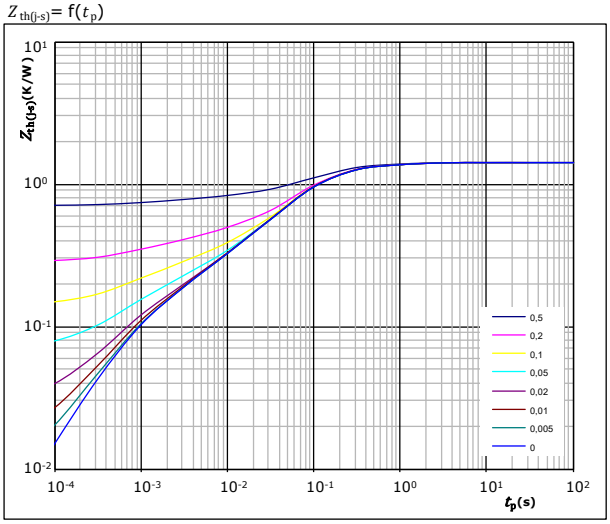


t_p =	100	µs		25 °C	
V_{DS} =	10	V	T_j:	125 °C	
				150 °C	

figure 4. **MOSFET**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	1,41	K/W

MOSFET thermal model values

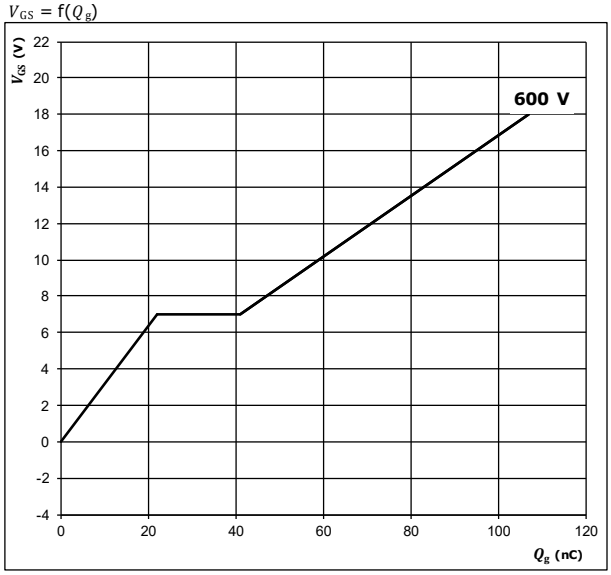
R (K/W)	τ (s)
1,24E-01	1,00E+00
3,91E-01	1,66E-01
6,76E-01	6,11E-02
1,21E-01	5,50E-03
9,55E-02	8,02E-04

H-Bridge Switch Characteristics

figure 5. **MOSFET**

Gate voltage vs Gate charge

$V_{GS} = f(Q_g)$



At

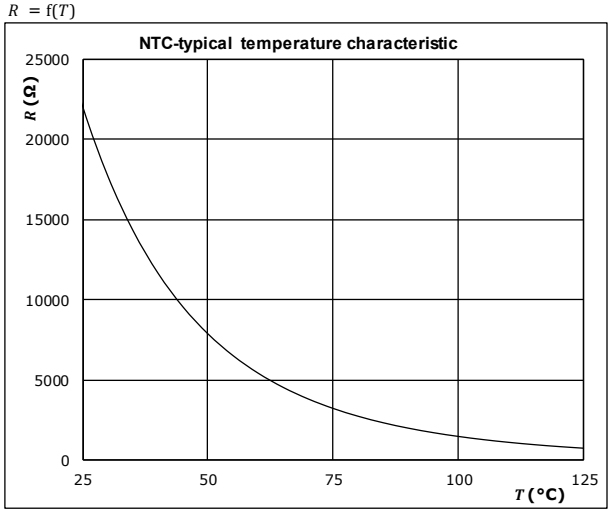
I_C = 20 A

Thermistor Characteristics

figure 1. **Thermistor**

Typical NTC characteristic as a function of temperature

$R = f(T)$

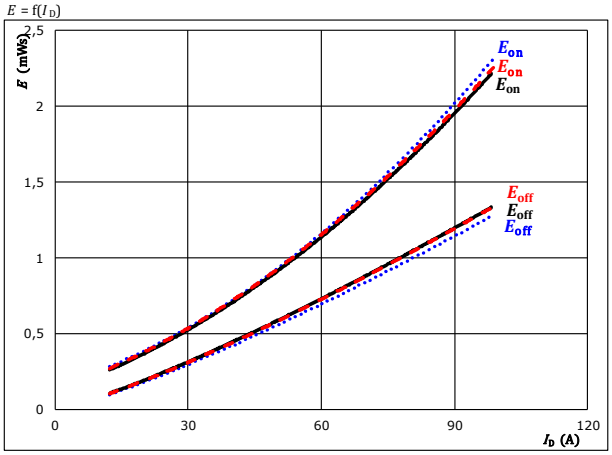


H-Bridge Switching Characteristics

figure 1. **MOSFET**

Typical switching energy losses as a function of drain current

$E = f(I_D)$



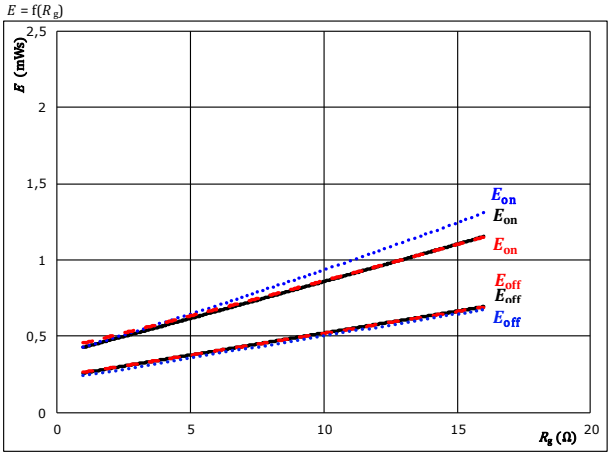
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
R_{gon} =	4	Ω		150 °C
R_{goff} =	4	Ω		

figure 2. **MOSFET**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



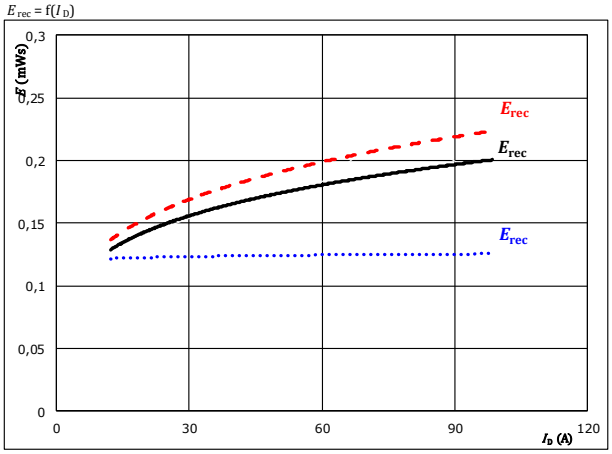
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
I_D =	33	A		150 °C

figure 3. **FWD**

Typical reverse recovered energy loss as a function of drain current

$E_{rec} = f(I_D)$



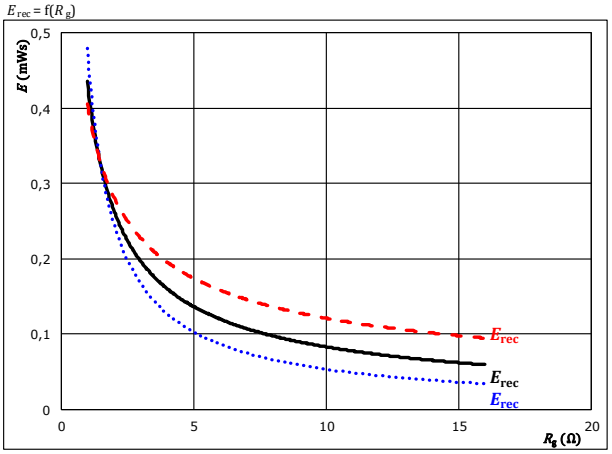
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

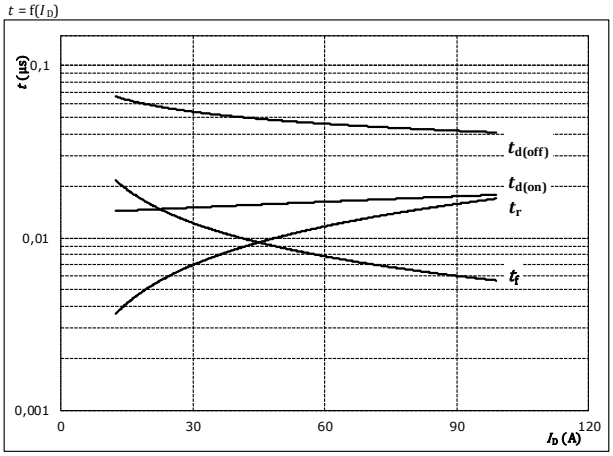
V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
I_D =	33	A		150 °C

H-Bridge Switching Characteristics

figure 5. **MOSFET**

Typical switching times as a function of drain current

$t = f(I_D)$



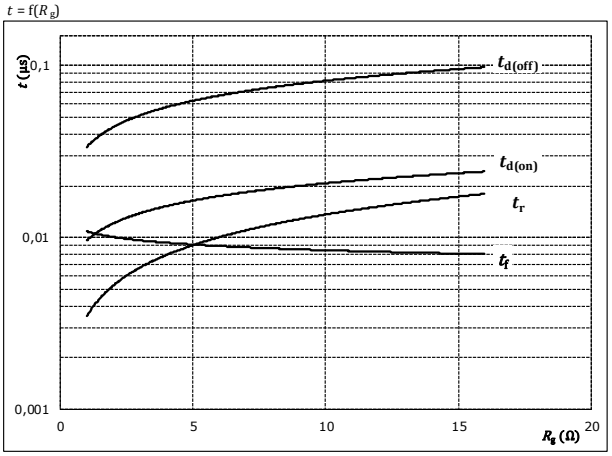
With an inductive load at

T_j =	150	°C
V_{DS} =	700	V
V_{GS} =	-4 / 16	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 6. **MOSFET**

Typical switching times as a function of gate resistor

$t = f(R_g)$



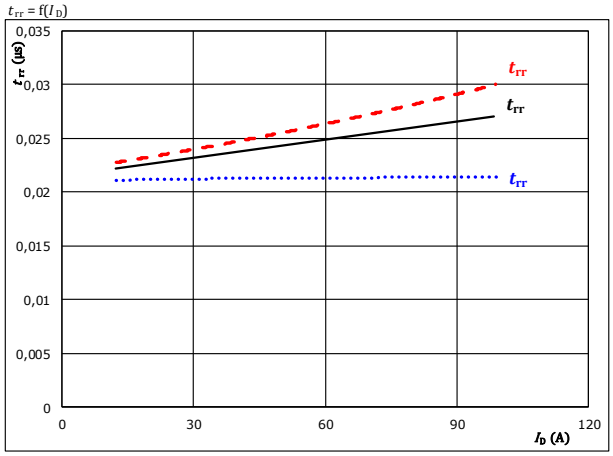
With an inductive load at

T_j =	150	°C
V_{DS} =	700	V
V_{GS} =	-4 / 16	V
I_D =	33	A

figure 7. **FWD**

Typical reverse recovery time as a function of drain current

$t_{rr} = f(I_D)$



With an inductive load at

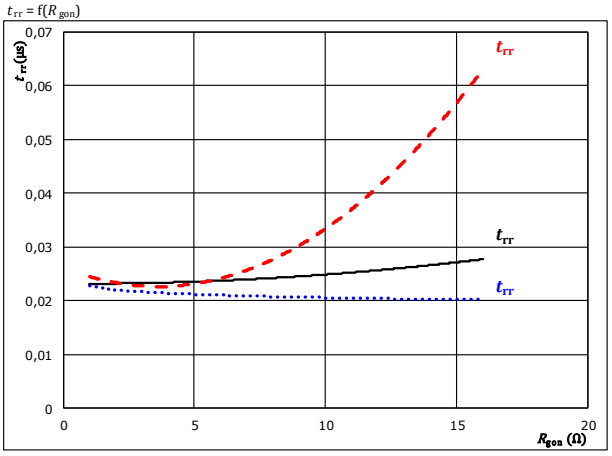
V_{DS} =	700	V
V_{GS} =	-4 / 16	V
R_{gon} =	4	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 8. **FWD**

Typical reverse recovery time as a function of MOSFET turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{DS} =	700	V
V_{GS} =	-4 / 16	V
I_D =	33	A

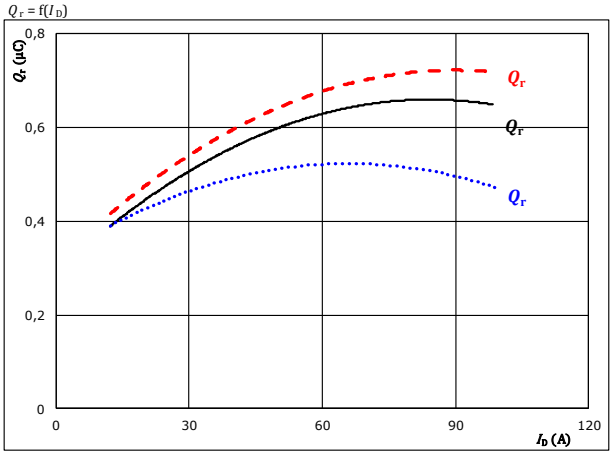
T_j: 25 °C, 125 °C, 150 °C

H-Bridge Switching Characteristics

figure 9. **FWD**

Typical recovered charge as a function of drain current

$Q_r = f(I_D)$



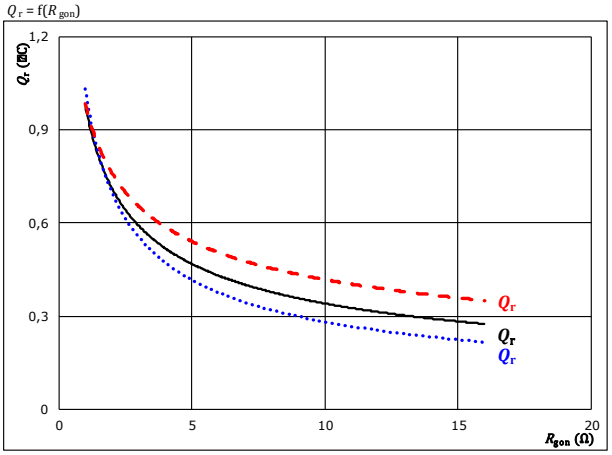
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 10. **FWD**

Typical recovered charge as a function of MOSFET turn on gate resistor

$Q_r = f(R_{gon})$



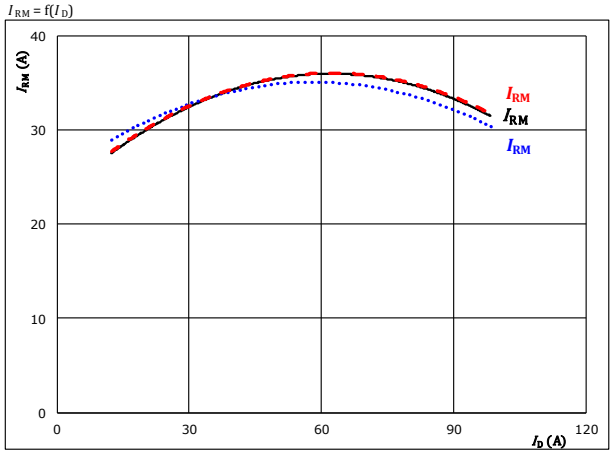
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
I_D =	33	A		150 °C

figure 11. **FWD**

Typical peak reverse recovery current current as a function of drain current

$I_{RM} = f(I_D)$



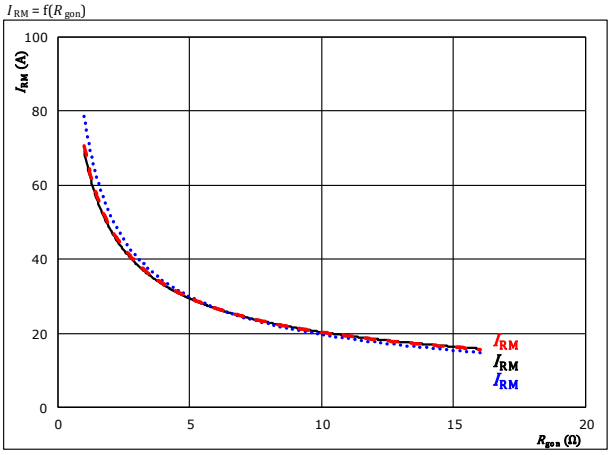
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 12. **FWD**

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$I_{RM} = f(R_{gon})$



With an inductive load at

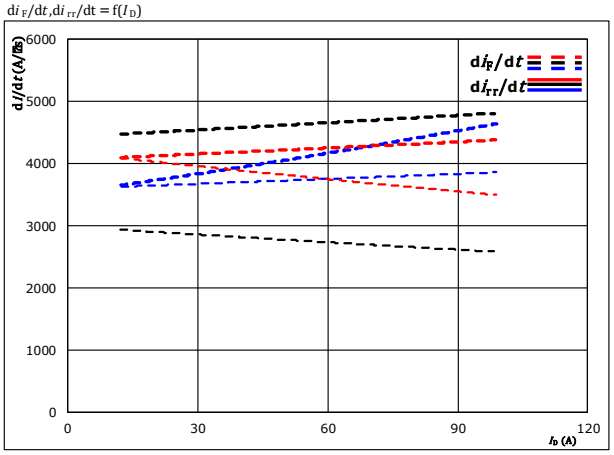
V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
I_D =	33	A		150 °C

H-Bridge Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of drain current

$di_F/dt, di_{rr}/dt = f(I_D)$



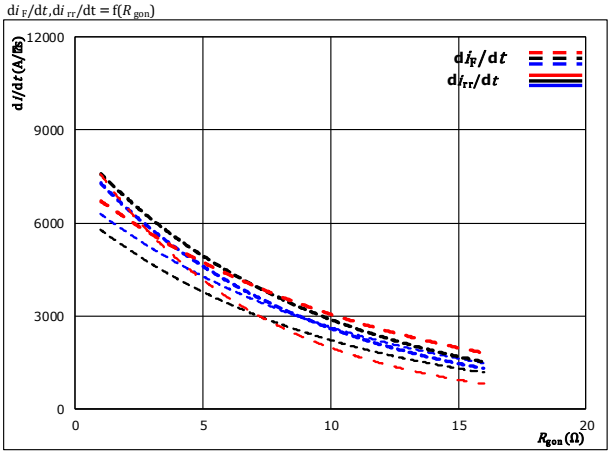
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of MOSFET turn on gate resistor

$di_F/dt, di_{rr}/dt = f(R_{gon})$



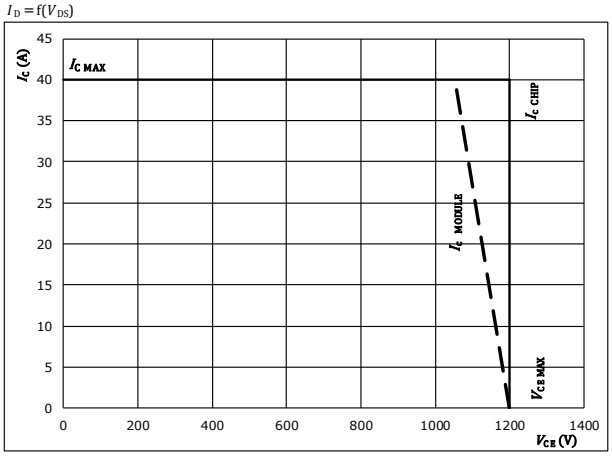
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	-4 / 16	V		125 °C
I_D =	33	A		150 °C

figure 15. **MOSFET**

Reverse bias safe operating area

$I_D = f(V_{DS})$



At

T_j =	150	°C
R_{gon} =	4	Ω
R_{goff} =	4	Ω

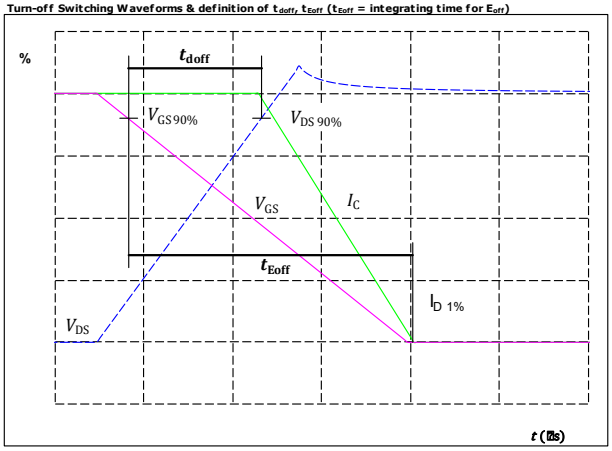
H-Bridge Switching Definitions

General conditions

T_j	=	**150 °C**
R_{gon}	=	**4 Ω**
R_{goff}	=	**4 Ω**

figure 1. **IGBT**

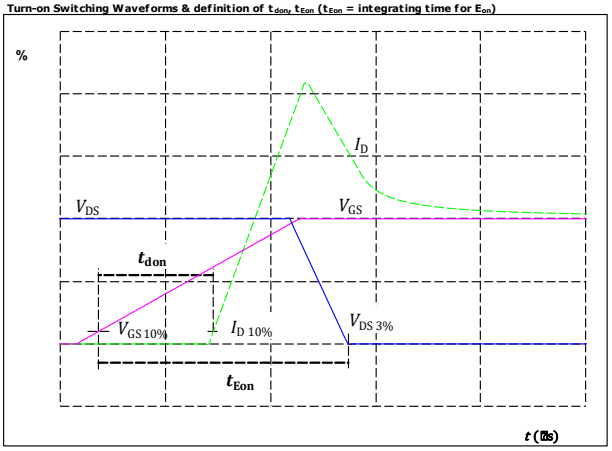
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GS}(0\%)$ =	-4	V
$V_{GS}(100\%)$ =	16	V
$V_{DS}(100\%)$ =	700	V
$I_D(100\%)$ =	33	A
t_{doff} =	53	ns

figure 2. **IGBT**

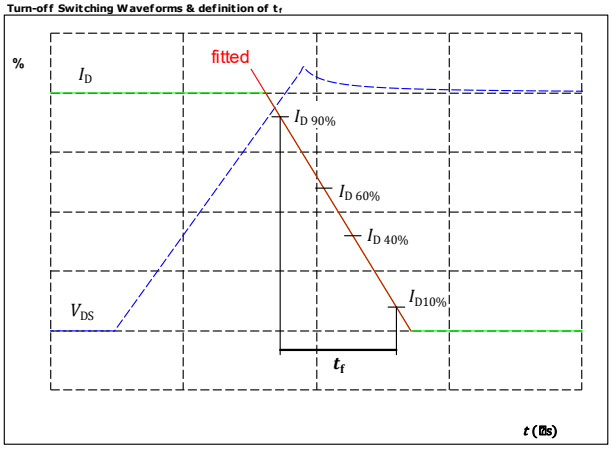
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GS}(0\%)$ =	-4	V
$V_{GS}(100\%)$ =	16	V
$V_{DS}(100\%)$ =	700	V
$I_D(100\%)$ =	33	A
t_{don} =	15	ns

figure 3. **IGBT**

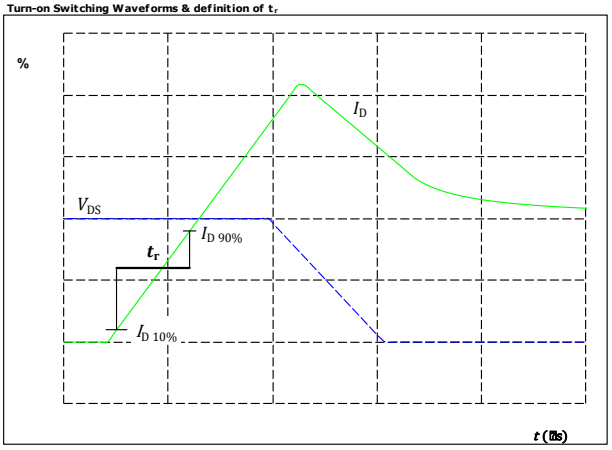
Turn-off Switching Waveforms & definition of t_f



$V_{DS}(100\%)$ =	700	V
$I_D(100\%)$ =	33	A
t_f =	8	ns

figure 4. **IGBT**

Turn-on Switching Waveforms & definition of t_r

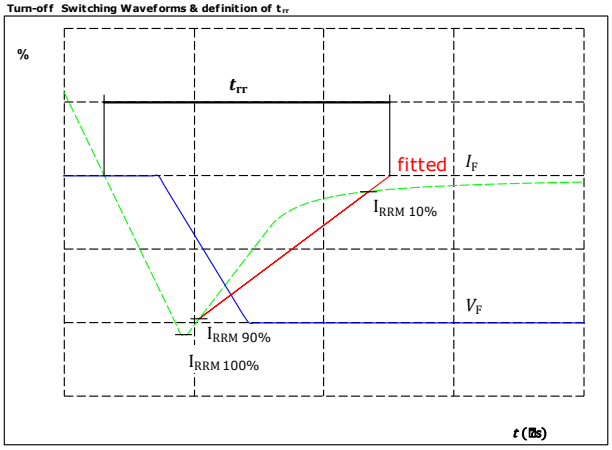


$V_{DS}(100\%)$ =	700	V
$I_D(100\%)$ =	33	A
t_r =	7	ns

H-Bridge Switching Characteristics

figure 5. **FWD**

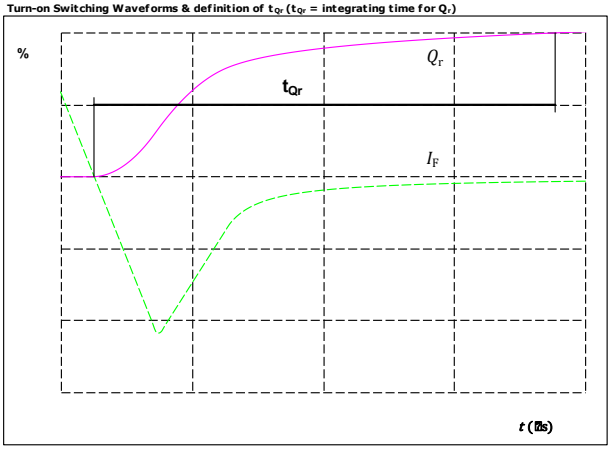
Turn-off Switching Waveforms & definition of t_{rr}



$V_F(100\%)$ =	700	V
$I_F(100\%)$ =	33	A
$I_{RRM}(100\%)$ =	33	A
t_{rr} =	24	ns

figure 6. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



$I_F(100\%)$ =	33	A
$Q_r(100\%)$ =	1	µC

Vincotech

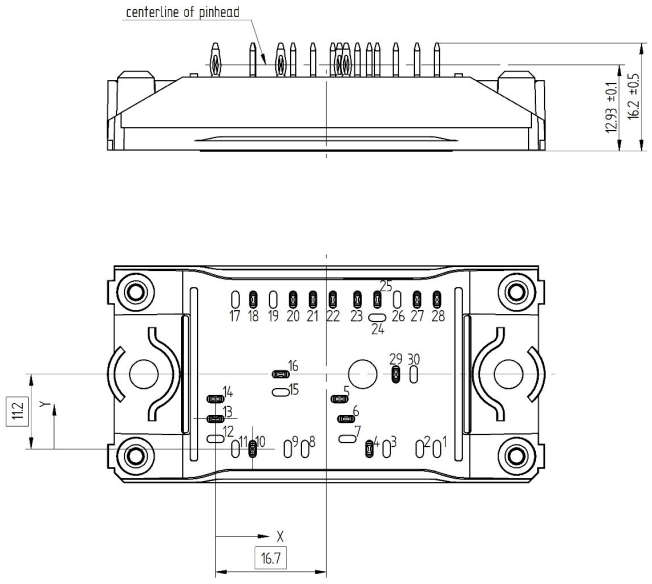
Ordering Code & Marking

Version	Ordering Code
without thermal paste 12 mm housing with Press-fit pins	10-PC124PA040MR-L638F18Y
with thermal paste 12 mm housing with Press-fit pins	10-PC124PA040MR-L638F18Y-/3/

	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Type&Ver	**Lot number**	**Serial**	**Date code**		
Datamatrix	TTTTTTVV	LLLLL	SSSS	WWYY		

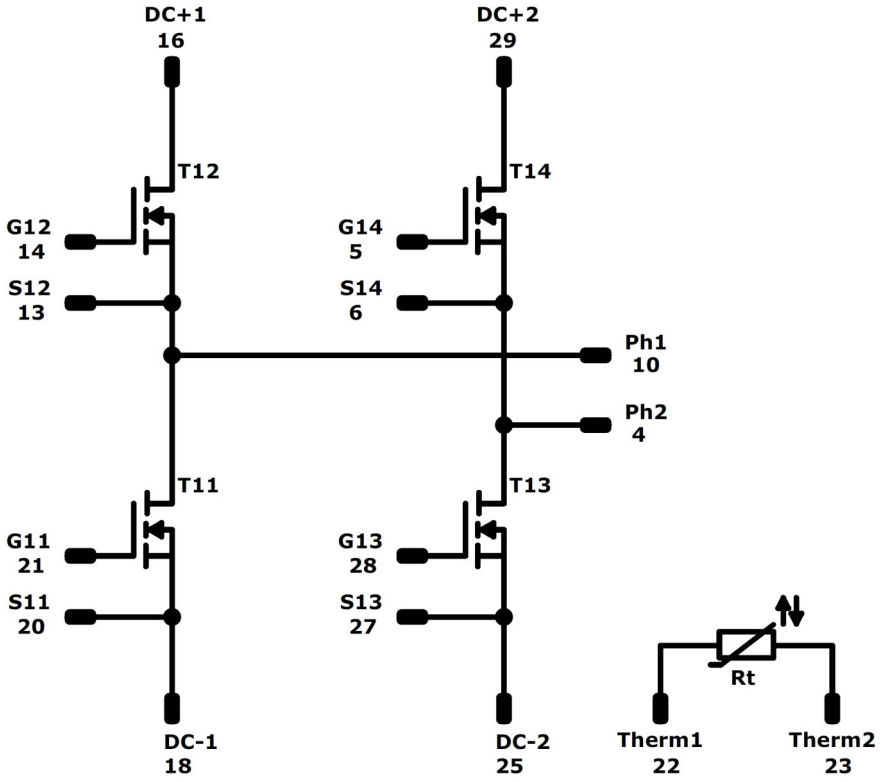
Outline

Pin table			
Pin	X	Y	Function
1	not assembled		
2	not assembled		
3	not assembled		
4	23,2	0	Ph2
5	18,7	7,5	G14
6	19,7	4,5	S14
7	not assembled		
8	not assembled		
9	not assembled		
10	5,6	0	Ph1
11	not assembled		
12	not assembled		
13	0	4,5	S12
14	0	7,5	G12
15	not assembled		
16	9,85	11,2	DC+1
17	not assembled		
18	5,7	22,4	DC-1
19	not assembled		
20	11,7	22,4	S11
21	14,7	22,4	G11
22	17,7	22,4	Therm1
23	21,4	22,4	Therm2
24	not assembled		
25	24,4	22,4	DC-2
26	not assembled		
27	30,4	22,4	S13
28	33,4	22,4	G13
29	27,2	11,2	DC+2
30	not assembled		



Tolerance of pinpositions: ±0,5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11 , T12 , T13 , T14	MOSFET	1200 V	40 mΩ	H-Bridge Switch	
Rt	NTC			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-PC124PA040MR-L638F18Y-D3-14	06 May. 2019	Correction of gate-source voltage, drain current, switching definitions	All